



- For 50 Ohm Source Impedance
- 7T Frequency of 298 MHz
- 1.0 Ohm Input Impedance
- 0.40 dB Noise Figure
- 30.0 dBm Max P<sub>IN</sub>
- 18.0 dBm Output IPa
- 28.0 dB Gain
- 10.0 dBm P<sub>1dB</sub>
- 1.22:1 Output VSWR
- Unconditional Stable, k>1
- Single Power Supply
- Single Power 3
- Non Magnetic

## **Specifications**

Summary of the key electrical specifications at room temperature

Index	Testing Item	Symbol	Test Constraints	Min	Nom	Max	Unit
1	Gain	S <sub>21</sub>	298 MHz	27.5	28.0	28.5	dB
2	Gain Variation	ΔG	298 MHz +/- 1 MHz		+/-0.05	+/- 0.1	dB
3	Input Impedance	RE [Zin]	298 MHz		1.0	2.0	Ohm
		IM [Zin]	298 MHz	-2.0	0	2.0	Ohm
4	Output VSWR, 50 Ohm Impedance	SWR <sub>2</sub>	298 MHz			1.22:1	Ratio
5	Reverse Isolation	S <sub>12</sub>	298 MHz	60	70		dB
6	Noise Figure	NF	298 MHz, Z <sub>s</sub> = 50 Ohm		0.40	0.50	dB
7	Output Power 1dB Compression Point	P <sub>1dB</sub>	298 MHz	8	10		dBm
8	Output-Third-Order Interception Point	IP <sub>3</sub>	Two-Tone, P <sub>out</sub> = 0 dBm each, 1 MHz separation	16	18		dBm
9	Current Consumption	I <sub>dd</sub>	V <sub>dd</sub> = +10.0 V		18		mA
10	Power Supply Operating Voltage	V <sub>dd</sub>		+7	+10	+12	V
11	Thermal Resistance	R <sub>th,c</sub>	Junction to case			220	°C/W
12	Operating Temperature	T₀		+10		+60	°C
13	Maximum RF Input Power	PIN, MAX	DC – 6.0 GHz, 10% Duty Cycle, $Z_s = 50$ Ohm			30	dBm
14	Saturate Recover Time	t <sub>sr</sub>	10% to 90% from 20 dBm Pin, $Z_s = 50$ Ohm		4	8	uS
15	ESD Protection, None Contact	V <sub>ESDN</sub>	Output Port			16	kV
16	ESD Protection, Direct Contact	VESD	Output Port			6	kV

## **Absolute Maximum Ratings**

Parameters	Units	Ratings				
DC Power Supply Voltage	V	12.0				
Drain Current	mA	30				
Total Power Dissipation	mW	350				
RF Input Power, 10% Duty Cycle	dBm	30				
Junction Temperature	°C	150				
Storage Temperature	°C	-65 ~ 150				
Operating Temperature	°C	0 ~ +70				
Thermal Resistance <sup>1</sup>	°C/W	220				
Operation of this device beyond any one of these parameters may cause permanent damage.						

## **Functional Block Diagram**



<sup>1</sup> The last stage transistor dominates the heat dissipation. The drain bias voltage is +3.5V and the drain current is 10.0 mA. The total power dissipation of the last stage transistor is thus 35 mW. The junction temperature arise  $0.035 \times 220 = 7.7$  ( $^{\circ}$ C).

# Product Description

CAUTION:

With its low input impedance, WMA7RC is designed for 50 Ohm source impedance multichannel coil applications. The pre-amp maintains excellent noise figure performance over source impedance variation that either comes from the different loads to the coils or not ideal design implementation of the coils. Moreover, the pre-amp allows higher source impedance design to increase the blocking impedance while maintaining superior SNR due to large equal noise circles. The amplifier has 0.50" x 0.40" x 0.10" surface mount package.

## Applications

Magnetic Resonance
Imaging

**REV D** 

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- RF Measurement
- Medical
- Current Sensor



Specifications and information are subject to change without notice.



## **Ordering Information**

Model Number WMA7RC

ESD tube is used for the packing. Contact factory for tape and reel packing option for higher volume order.

## **Typical Data**



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## **Outline**

## Foot Print/Mounting Layout



## **Application Notes:**

#### A. Motherboard Layout

The recommended motherboard layout is shown in diagram of **Foot Print/Mounting Layout**. Sufficient numbers of ground vias on center ground pad are essential for the RF grounding. The width of the 50-Ohm microstrip lines at the input and output RF ports may be different for different property of the substrate. The ground plane on the backside of the substrate is needed to connect the center ground pad through the vias. The ground plane is also essential for the 50-Ohm microstrip line launches at the input and output ports.

The +10V DC voltage is applied at Pin 4 or at the output Pin 5. There is a built-in bias-T at the output port to separate the RF output signal and input +10V DC power supply.



Fig. 1 Example of the motherboard



Fig. 2 Dispensed solder paste



Fig. 3 Assembled

#### B. Assembly

The regular low temperature and none clean solder paste such as SN63 is recommended. The high temperature solder has been used internally for the WHM series amplifier assembly. The melting temperature point of the high temperature solder is around 217  $\sim$  220  $^{\circ}$ C. Thus, melting temperature of the solder paste should be below 217  $^{\circ}$ C for assembling WHM series amplifier on the test board to reduce the possible damage. The temperature melting point of the SN63 solder paste is around 183  $^{\circ}$ C and is suitable for the assembly purpose.

The SN63 solder paste can be dispensed by a needle manually or driven by a compressed air. **Figure 2** shows the example of the dispensed solder paste pattern. Each solder paste dot is in the diameter of  $0.005^{\circ} \sim 0.010^{\circ}$  ( $0.125 \sim 0.250$  mm).

For volume assembly, a stencil with 0.006" (0.15 mm) is recommended to print the solder paste on the circuit board.

For more detail assembly process, refer to AN-109 at <u>www.wantcominc.com</u> website.

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